



SOT-89 Plastic-Encapsulated Transistors

2SA1201 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM} : 500 \text{ mW (Tamb=25°C)}$$

Collector current

$$I_{CM} : -800 \text{ mA}$$

Collector-base voltage

$$V_{(BR)CBO} : -120 \text{ V}$$

Operating and storage junction temperature range

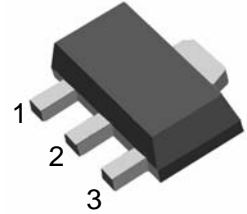
$$T_J, T_{stg}: -55°C \text{ to } +150°C$$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-120\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5\text{V}, I_C=-500\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$			30	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	80-160	120-240
Marking	DO	DY